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ABSTRACT

A method of manufacturing a semiconductor device, comprising: a first step of interposing an anisotropic conductive material 16 between a surface 18 of a substrate 12 on which an interconnect pattern 10 is formed, and a surface 24 of a semiconductor chip 20 on which electrodes 22 is formed; and a second step in which pressure is applied between the semiconductor chip 20 and the substrate 12, the interconnect pattern 10 and electrodes 22 are electrically connected, and the anisotropic conductive material 16 is caused to surround at least a part of a lateral surface 28 of the semiconductor chip 20.